

DESCRIPTION

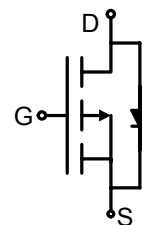
The SSF2301B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

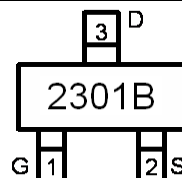
- $V_{DS} = -20V, I_D = -2.8A$
 $R_{DS(ON)} < 150m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT23 top view

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2301B	SSF2301B	SOT23	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	-2.8	A
	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			±100	nA

ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.45		-1	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-2.8A		80	100	
		V _{GS} =-2.5V, I _D =-2A		110	150	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-2.8A		9		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-10V, V _{GS} =0V, F=1.0MHz		1160		PF
Output Capacitance	C _{OSS}			210		PF
Reverse Transfer Capacitance	C _{RSS}			125		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, I _D =-2.8A V _{GS} =-4.5V, R _{GEN} =3Ω		13.6	27.2	nS
Turn-on Rise Time	t _r			8.6	17.2	nS
Turn-Off Delay Time	t _{d(off)}			73.6	147.2	nS
Turn-Off Fall Time	t _f			34.6	69.2	nS
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-2.8A, V _{GS} =-4.5V		9.6	12.7	nC
Gate-Source Charge	Q _{gs}			1.1		nC
Gate-Drain Charge	Q _{gd}			2.6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-0.75A			-1.2	V
Diode Forward Current (Note 2)	I _S				-2.8	A

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

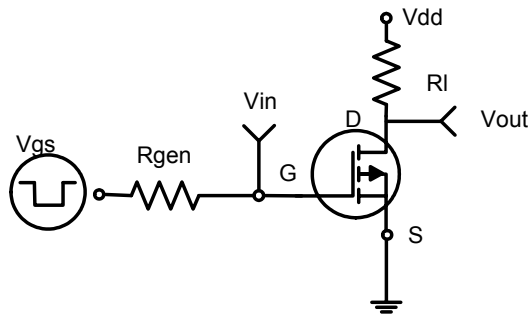


Figure1:Switching Test Circuit

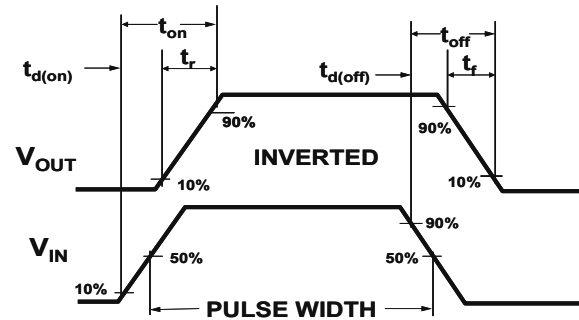


Figure 2:Switching Waveforms

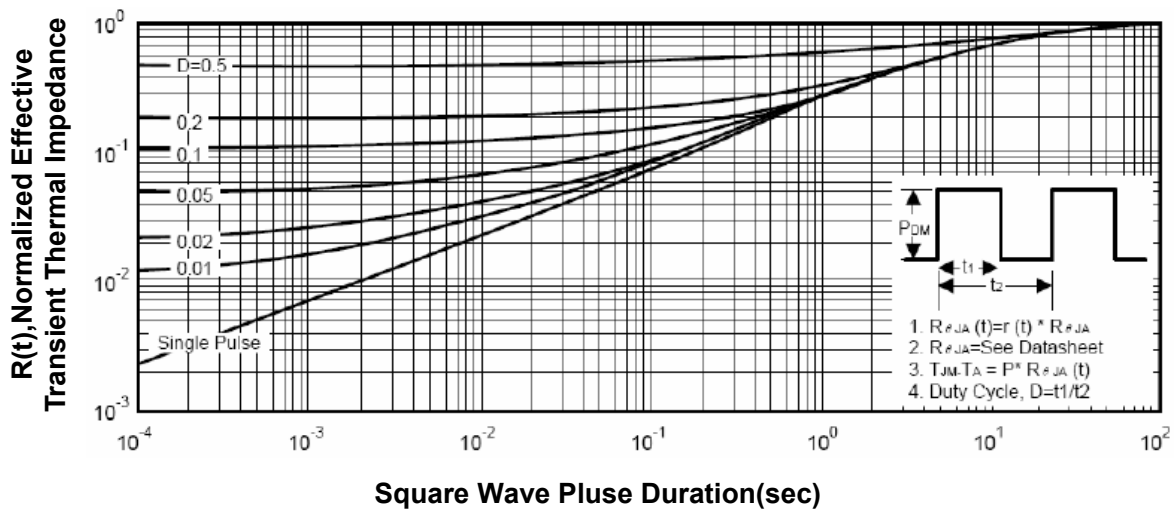
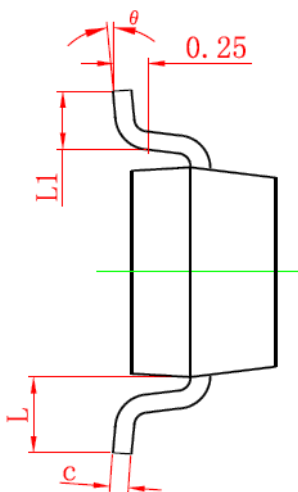
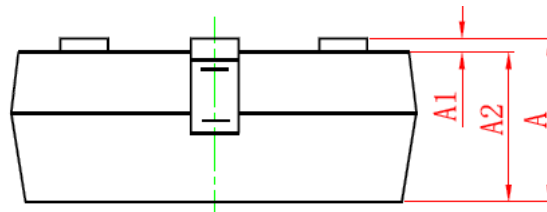
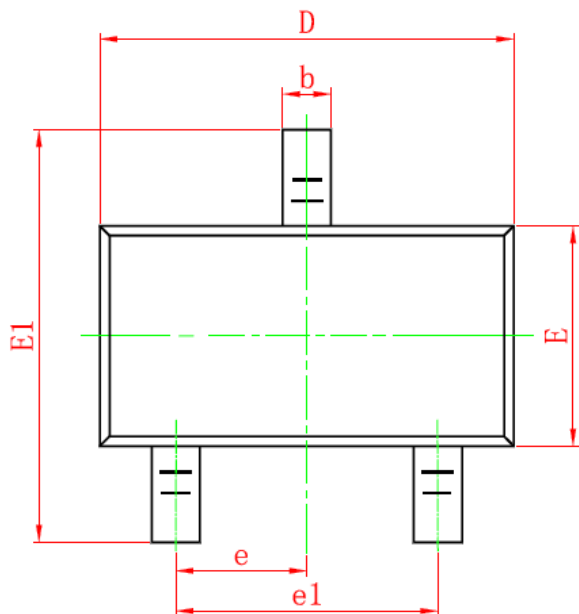


Figure 3: Normalized Maximum Transient Thermal Impedance

SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

NOTES

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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